TOSHIBA Transistor Silicon NPN Triple Diffused Type (Darlington)

2SD1409A

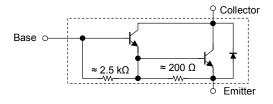
High Voltage Switching Applications

- High DC current gain: $h_{FE} = 600$ (min.) (VCE = 2 V, $I_{C} = 2$ A)
- Monolithic construction with built-in base-emitter shunt resistor

Maximum Ratings (Ta = 25°C)

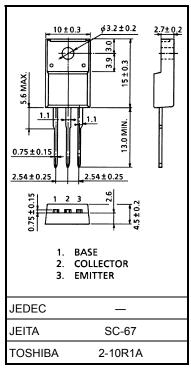
Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	600	V	
Collector-emitter voltage		V _{CEO}	400	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current		Ic	6	Α	
Base current		Ι _Β	1	Α	
Collector power dissipation	Ta = 25°C	Pc	2.0	W	
	Tc = 25°C		25		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Equivalent Circuit



Industrial Applications

Unit: mm

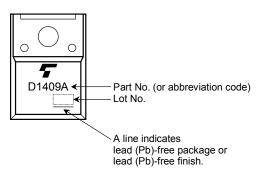


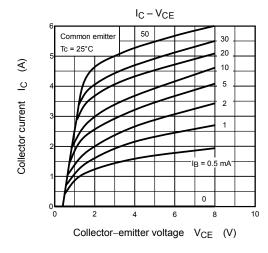
Weight: 1.7 g (typ.)

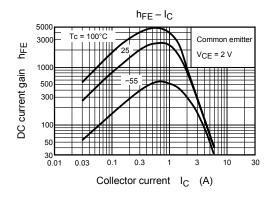
Electrical Characteristics (Ta = 25°C)

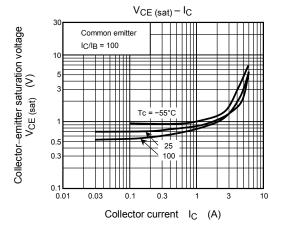
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	urrent	I _{CBO}	V _{CB} = 600 V, I _E = 0	_	_	0.5	mA
Emitter cut-off cur	rent	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	3	mA
Collector-emitter I	oreakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	400	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 2 V, I _C = 2 A	600	_	_	
		h _{FE (2)}	V _{CE} = 2 V, I _C = 4 A	100	_	_	
Collector-emitter	saturation voltage	V _{CE (sat)}	I _C = 4 A, I _B = 0.04 A	_	_	2.0	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 4 A, I _B = 0.04 A	_	_	2.5	V
Emitter-collector f	orward voltage	V _{ECF}	I _E = 4 A, I _B = 0	-	_	3.0	V
Collector output capacitance		C _{ob}	V _{CB} = 50 V, I _E = 0, f = 1 MHz	_	35	_	pF
	Turn-on time	t _{on}	20 μs Input 1 1 1 1 20 1 10	_	1	_	
	Storage time	t _{stg}		_	8	_	μs
	Fall time	t _f		_	5	_	

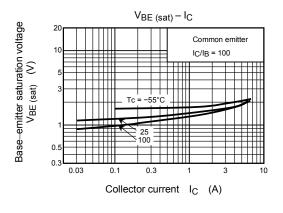
Marking

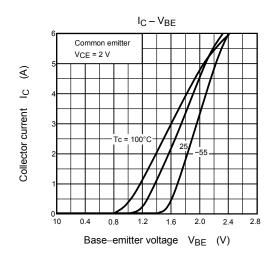


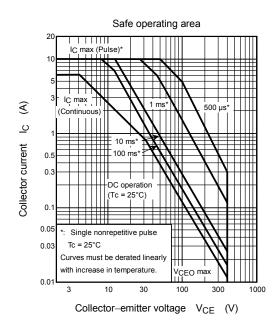


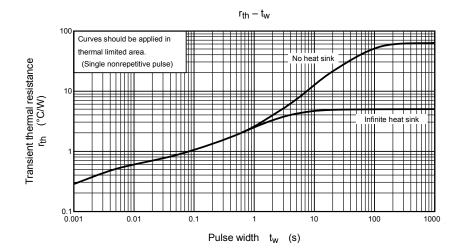












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